

**2N2906A, L JAN, JTX, JTXV, JANS**  
**2N2906AUA JAN, JTX, JTXV, JANS**  
**2N2906AUB JAN, JTX, JTXV, JANS**  
**2N2907A, L JAN, JTX, JTXV, JANS**  
**2N2907AUA JAN, JTX, JTXV, JANS**  
**2N2907AUB JAN, JTX, JTXV, JANS**



Processed per MIL-PRF-19500/291

**PNP SILICON SMALL-SIGNAL TRANSISTORS**

**MAXIMUM RATINGS**

Ratings	Symbol	All Types		Units
Collector-Emitter Voltage	$V_{CE0}$	60		Vdc
Collector-Base Voltage	$V_{CBO}$	60		Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0		Vdc
Collector Current	$I_C$	600		mAdc
		<b>A, L, AUB<sup>(1)</sup></b>	<b>AUA<sup>(2)</sup></b>	
Total Power Dissipation @ $T_A = 25^{\circ}C$	$P_T$	0.5	0.65	W
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200		$^{\circ}C$

1) Derate linearly 3.08 mW/ $^{\circ}C$  above  $T_A = +37.5^{\circ}C$ .

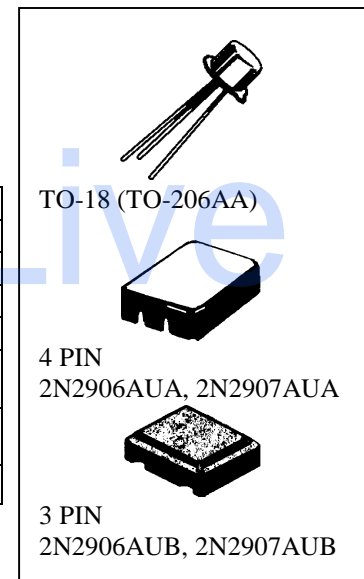
2) Derate linearly 4.76 mW/ $^{\circ}C$  above  $T_A = +63.5^{\circ}C$ .

**ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$  unless otherwise noted)**

Characteristics	Symbol	Min.	Max.	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage $I_C = 10$ mAdc	$V_{(BR)CEO}$	60		Vdc
Collector-Base Cutoff Current $V_{CE} = 60$ Vdc	$I_{CBO1}$		10	$\mu$ Adc
Collector-Base Cutoff Current $V_{CE} = 50$ Vdc	$I_{CBO}$		10	$\eta$ Adc
Collector-Base Cutoff Current $V_{CE} = 50$ Vdc	$I_{CES}$		50	$\eta$ Adc
Emitter-Base Cutoff Current $V_{EB} = 5.0$ Vdc	$I_{EBO1}$		10	$\mu$ Adc
Emitter-Base Cutoff Current $V_{EB} = 4.0$ Vdc	$I_{EBO}$		50	$\eta$ Adc



S2N2906A, L, AUA, AUB; S2N2907A, L, AUA, AUB JAN SERIES

**ELECTRICAL CHARACTERISTICS (con't)**

Characteristics	Symbol	Min.	Max.	Unit
<b>ON CHARACTERISTICS</b>				
Forward-Current Transfer Ratio I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub> = 10 Vdc S2N2906A., L, UA, UB S2N2907A, L, UA,UB	h <sub>FE</sub>	40		
I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc S2N2906A, L, UA, UB S2N2907A, L, UA, UB		75	175	
I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc S2N2906A., L, UA, UB S2N2907A, L, UA, UB		40	450	
I <sub>C</sub> = 150 mAdc, V <sub>CE</sub> = 10 Vdc S2N2906A, L, UA, UB S2N2907A, L, UA, UB		100		
I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc S2N2906A. L, UA, UB S2N2907A, L, UA, UB		40	120	
		100	300	
Collector-Emitter Saturation Voltage I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc	V <sub>CE(sat)</sub>		0.4 1.6	Vdc
Base-Emitter Saturation Voltage I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc	V <sub>BE(sat)</sub>	0.6	1.3 2.6	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Forward Current Transfer Ratio V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 1.0 mAdc, f = 1.0 kHz S2N2906A, L, UA,UB S2N2907A, L, UA,UB	h <sub>fe</sub>	40 100		
Magnitude of Small-Signal Forward Current Transfer Ratio V <sub>CE</sub> = 20 Vdc, I <sub>C</sub> = 20 mAdc, f = 100 MHz	h <sub>fe</sub>	2.0		
Output Capacitance V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, 100 kHz ≤ f ≤ 1.0 MHz	C <sub>obo</sub>		8.0	pF
Input Capacitance V <sub>EB</sub> = 2.0 Vdc, I <sub>C</sub> = 0, 100 kHz ≤ f ≤ 1.0 MHz	C <sub>ibo</sub>		30	pF